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Alternative for NAND Flash Innovation

Flash Memory Summit 2022



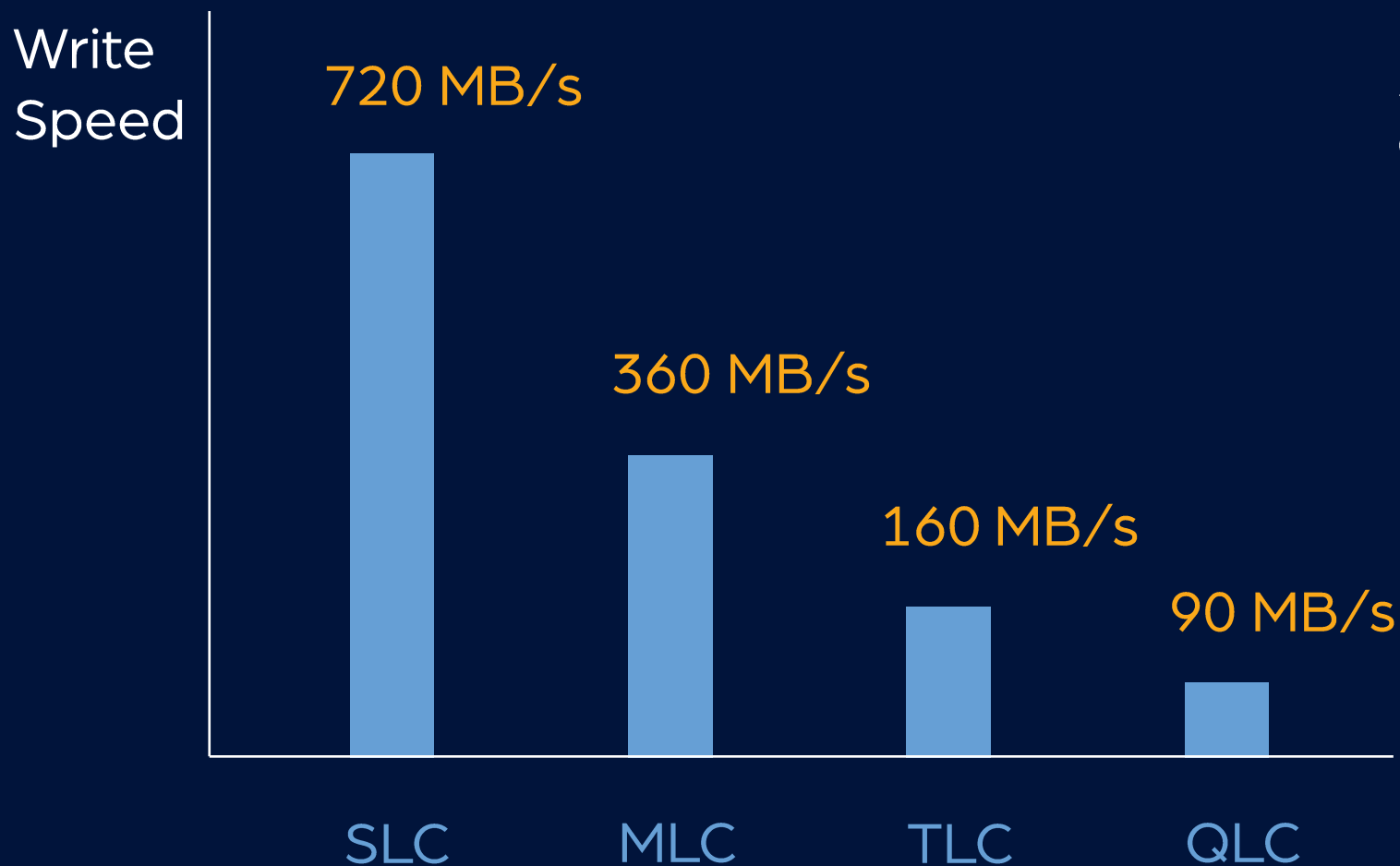
Andy Hsu | Founder and CEO

Andy has more than 25 years of experience in the semiconductor industry including positions as VP of Engineering and leader of R&D and engineering teams. He is an accomplished technology visionary and inventor of more than 120 granted U.S. patents.

<https://neosemic.com>

<https://www.linkedin.com/in/andy-hsu-neo/>

Each Generation's Speed Became Slower



* Vt – Threshold Voltage

Next Gen Memory Architecture

X-NAND™

0%

Die Size
Increase

3X

Random
R/W Speed

Gen1

10X

Sequential
Write Speed

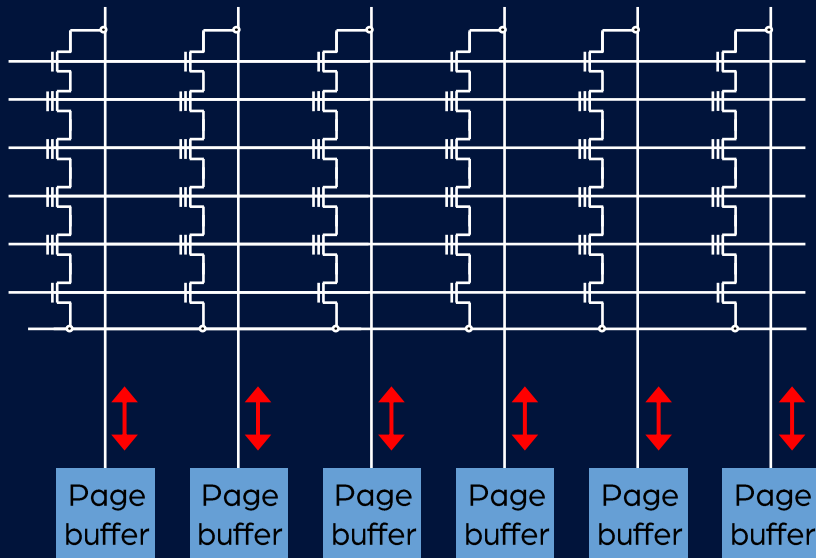
Gen2

20X

Sequential
Write Speed

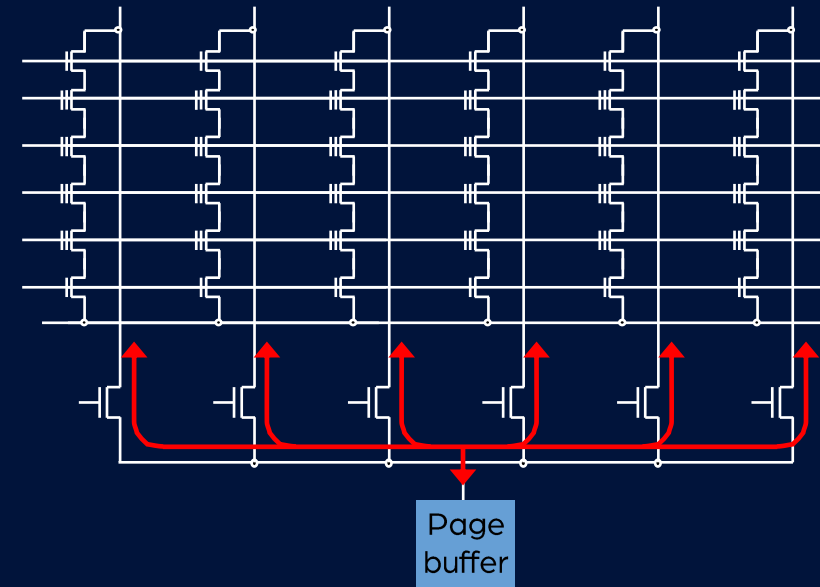
Page Buffer Architecture

Conventional NAND



One page buffer to read and write data to one bit line (BL).

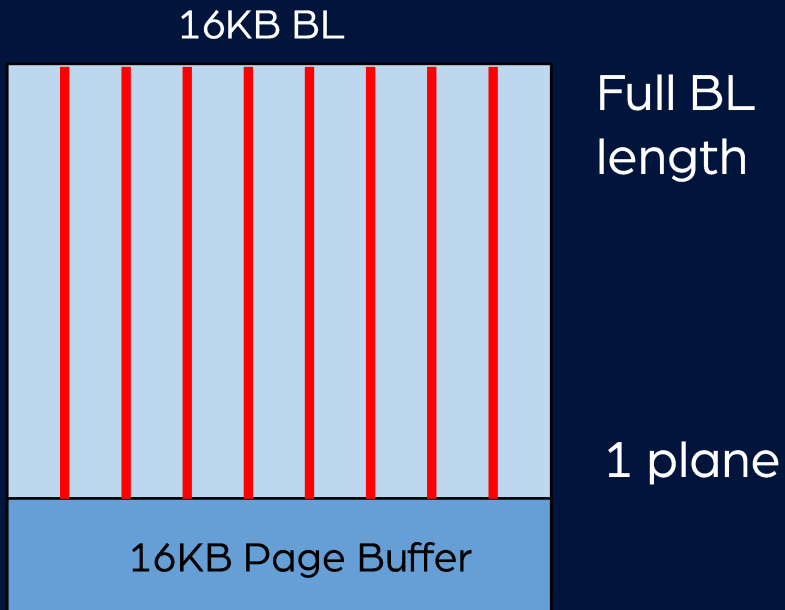
X-NAND



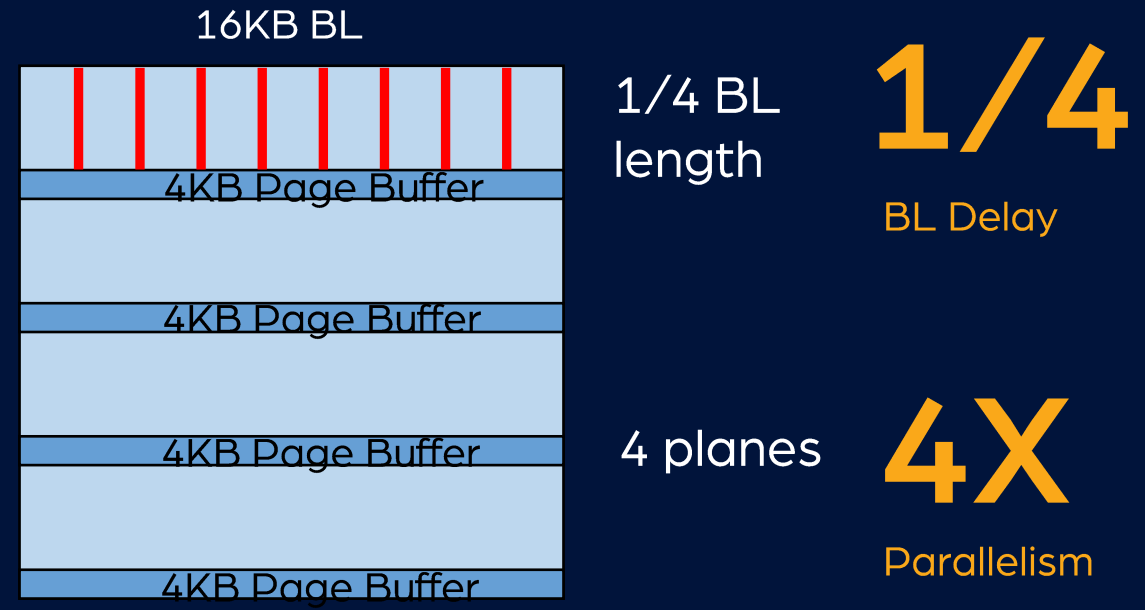
Shared page buffer to multiple bit lines and reduced layout size.

Bit Line Architecture

Conventional NAND



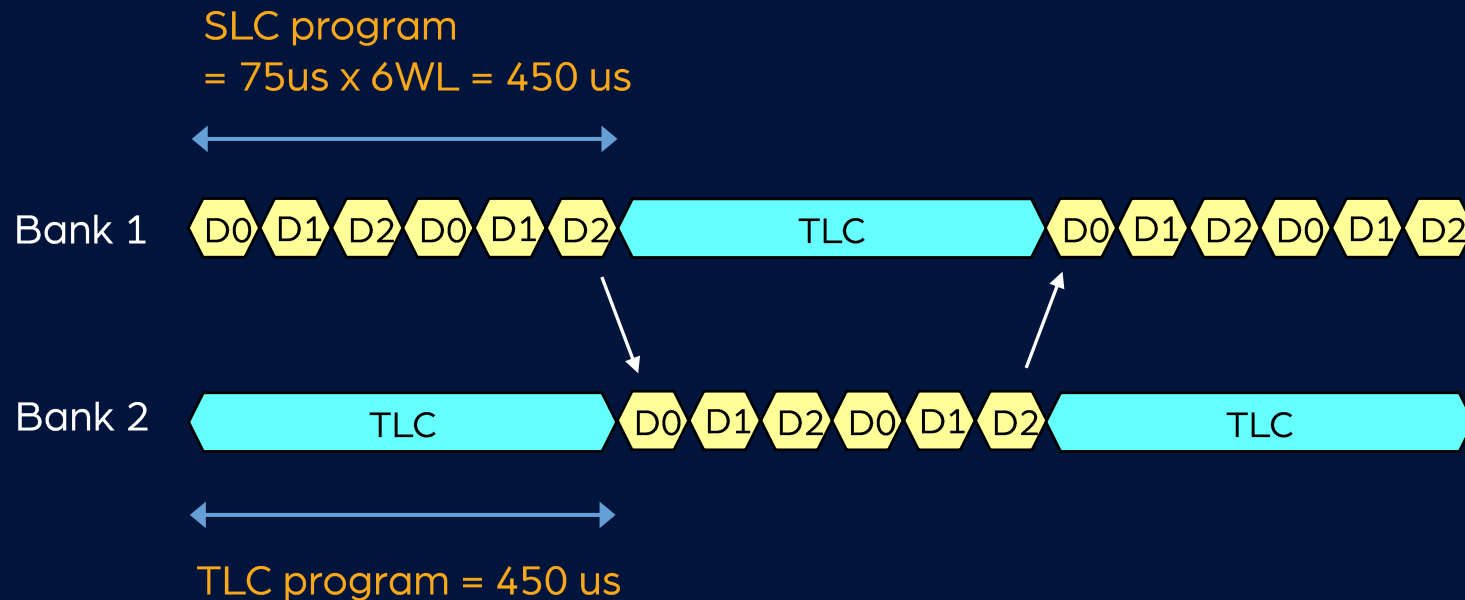
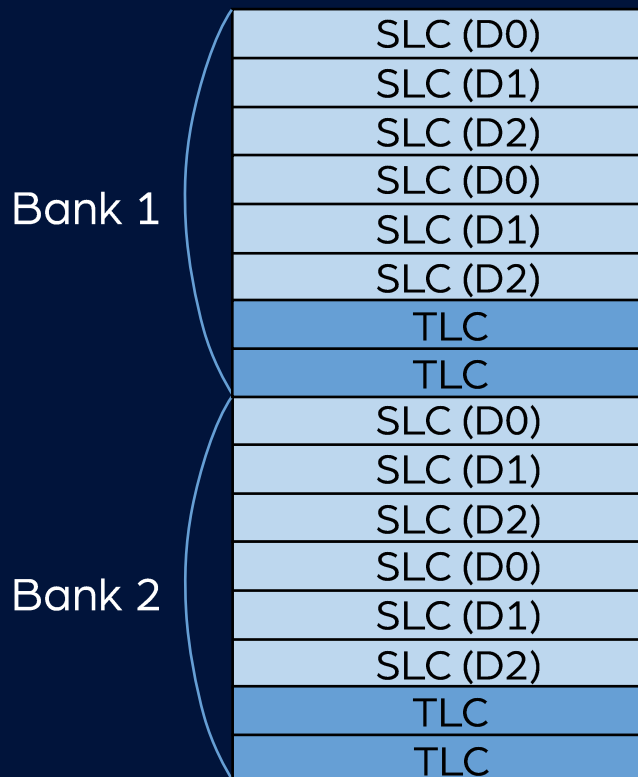
X-NAND



Shorter bit lines and more planes without increasing die size.

SLC/TLC Parallel-Programming

16 planes

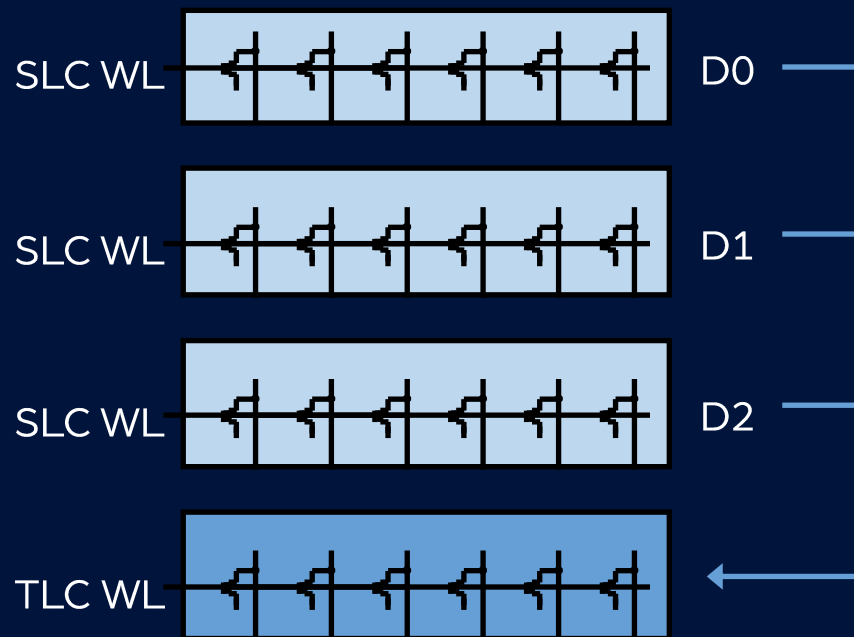


Data can be continuously programmed into TLC cells using SLC speed !

X-NAND Gen 1 vs. Gen 2

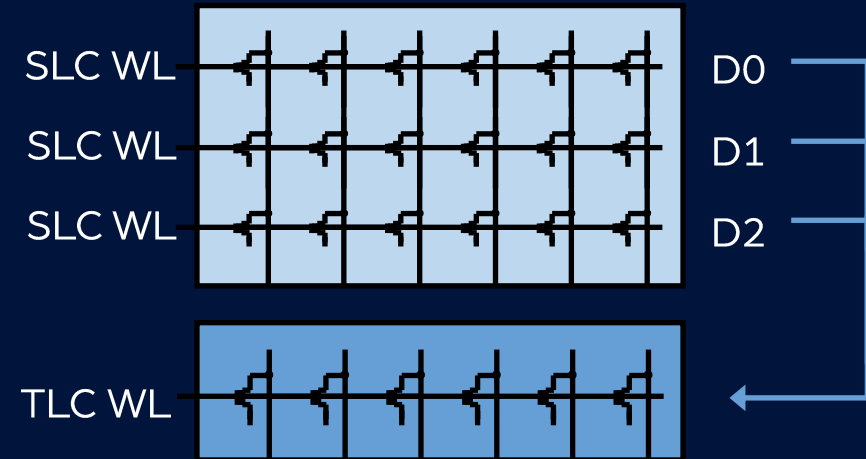
X-NAND Gen1

4 planes



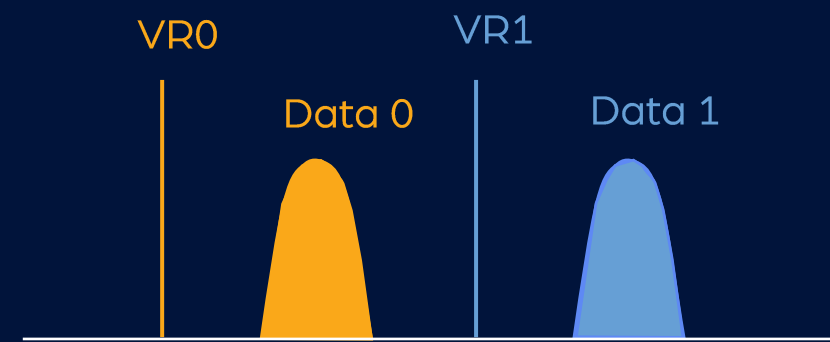
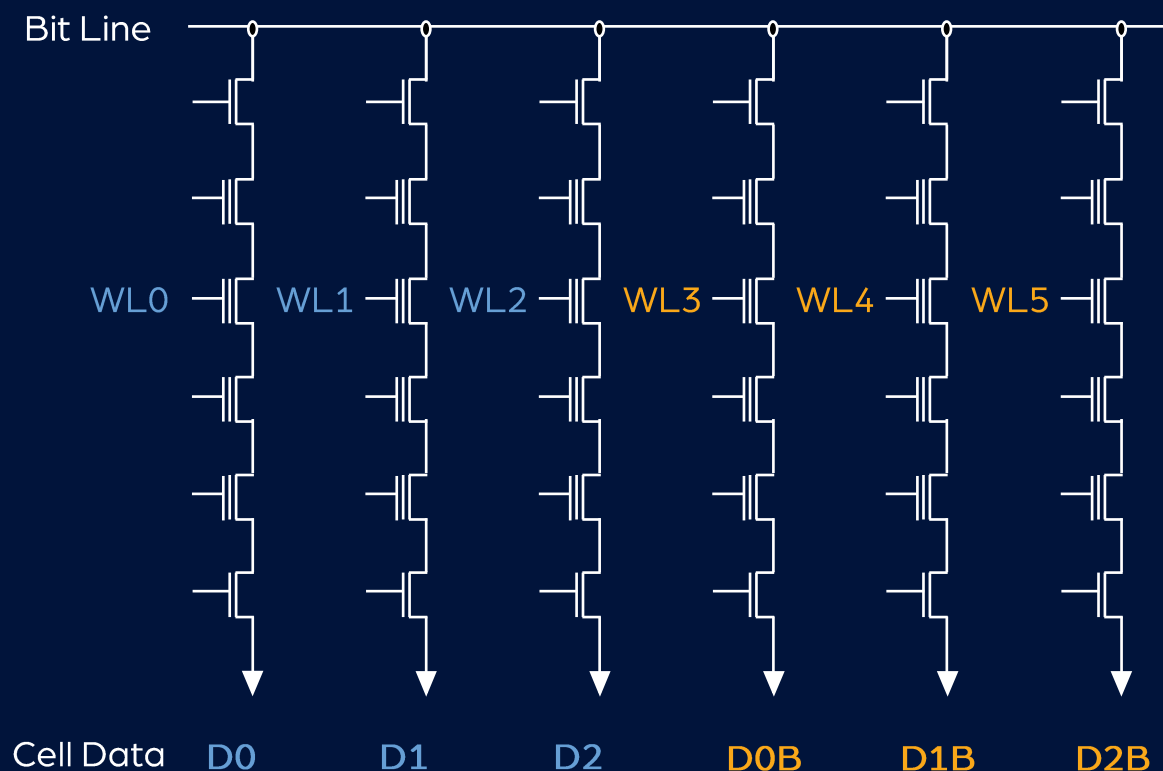
X-NAND Gen2

2 planes



2X Program Throughput

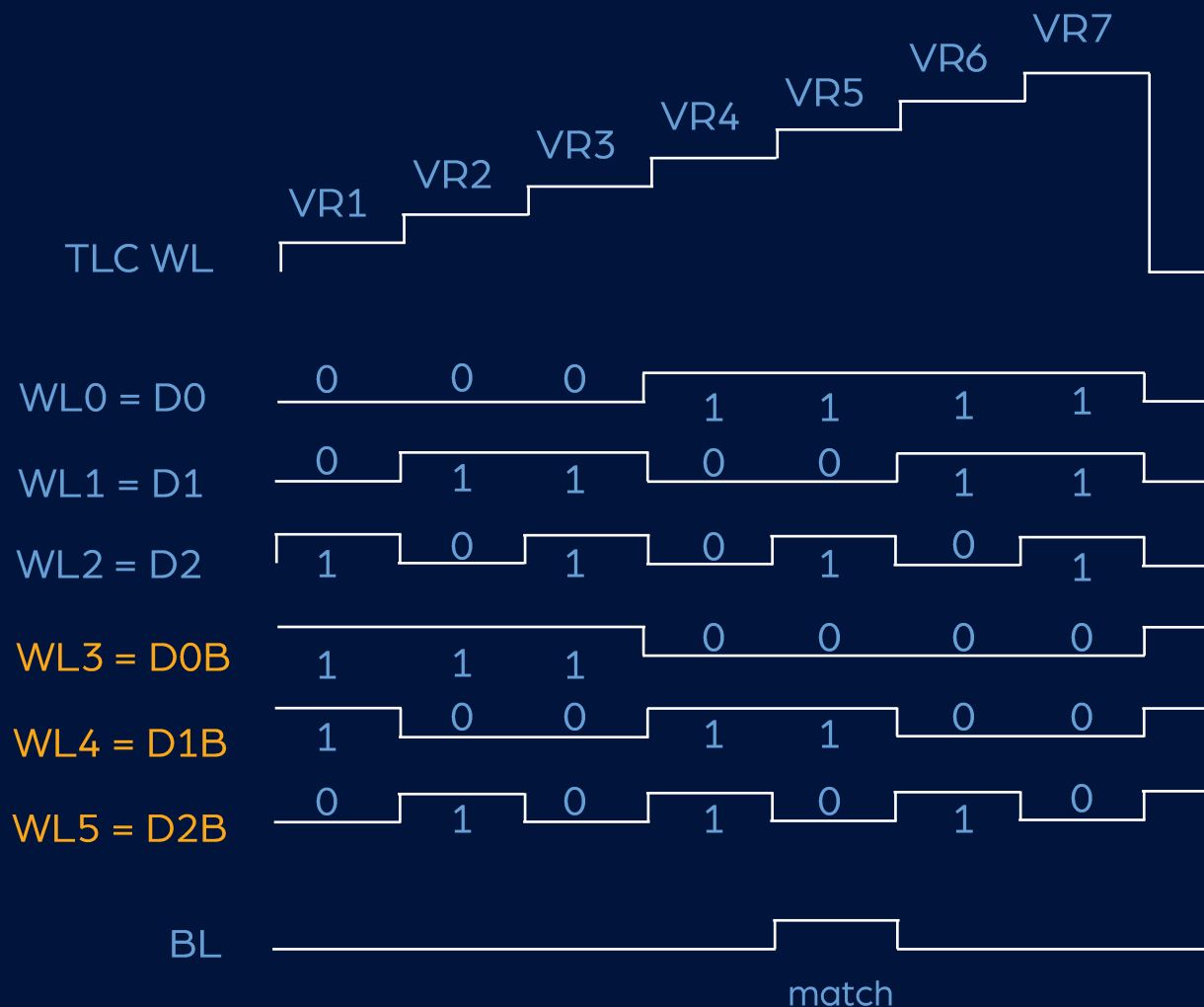
Data-Match Verification (DMV)



Cell = off when data is matched

X-NAND Gen2 uses a special DMV operation to match the data stored in three SLC word lines in one plane.

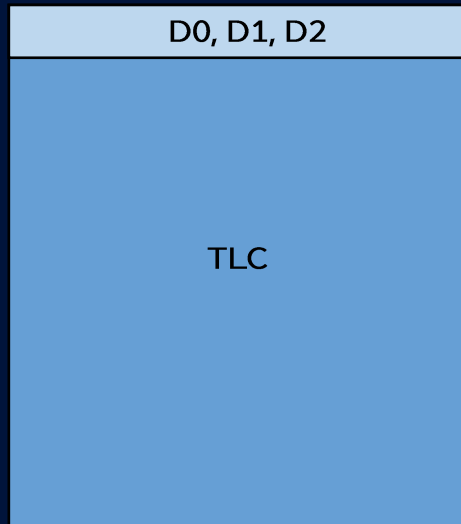
Data-Match Verification (DMV)



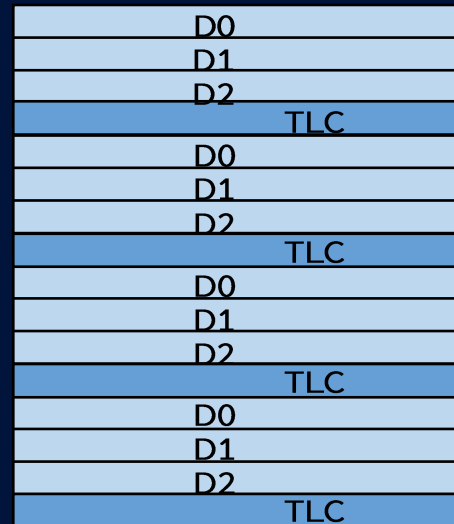
The SLC word lines are applied with sequential data from 000 to 111 to match the data stored in the cells.

TLC Program Throughput

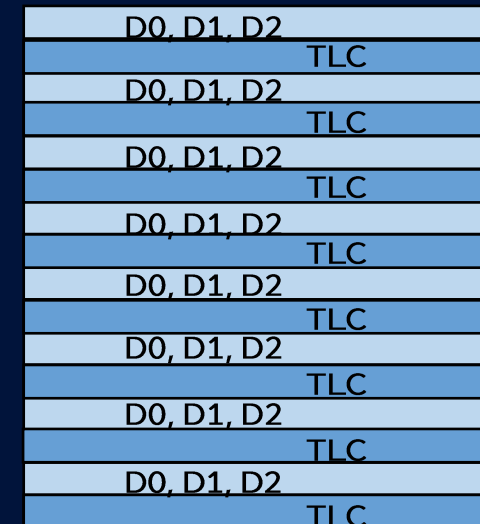
NAND
160MB/s



X-NAND Gen1
1.6GB/s



X-NAND Gen2
3.2GB/s



10X

20X

* Based on simulation



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Next Gen Memory Architectures